

RECEIVED
CENTRAL FAX CENTER

APR 16 2007

ABSTRACT OF THE DISCLOSURE

- A method and a system for improving the strength of connection
between a dielectric carrier substrate and a cover layer by obliquely
5 bombarding the substrate at at least one of its surfaces with high energy
heavy ion irradiation from two different angles to produce intersecting latent
ion traces therein which by subsequent chemical etching are formed into
intersecting recesses within which the cover layer may be anchored.